

	Hits	Search Text
1	35	semiconductor\$4.as. and yamazaki.in. and ((integrate\$3 near3 circuit\$3) IC\$3) adj2 card\$3
2	0	semiconductor\$4.as. and tachmura.in. and ((integrate\$3 near3 circuit\$3) IC\$3) adj2 card\$3 and (stack\$4 near displa\$3)
3	0	semiconductor\$4.as. and tachmura.in. and ((integrate\$3 near3 circuit\$3) IC\$3) adj2 card\$3
4	2	semiconductor\$4.as. and watanabe.in. and ((integrate\$3 near3 circuit\$3) IC\$3) adj2 card\$3
5	2936	(stack\$4 near displa\$3)
6	0	semiconductor\$4.as. and yamazaki.in. and ((integrate\$3 near3 circuit\$3) IC\$3) adj2 card\$3 and (stack\$4 near displa\$3)
7	48767	((integrate\$3 near3 circuit\$3) IC\$3) adj2 card\$3
8	14	((integrate\$3 near3 circuit\$3) IC\$3) adj2 card\$3 and (stack\$4 near displa\$3)
9	13836	(overlap\$7 near3 displa\$3)
10	1315	((integrate\$3 near3 circuit\$3) IC\$3) near2 (thin\$4 near2 film\$4)
11	205	((integrate\$3 near3 circuit\$3) IC\$3 ID\$3) adj2 card\$3 and ((overlap\$6) near displa\$3)
12	3	((integrate\$3 near3 circuit\$3) IC\$3 ID\$3) adj2 card\$3 same ((overlap\$6) near displa\$3)
13	24	S23 with S27
14	0	S11 same S12
15	4	S11 and S12
16	1051952	((integrate\$3 near3 circuit\$3) IC\$3)
17	471	S11 same S15
18	1015119	((integrate\$3 adj2 circuit\$3) IC\$2)
19	125	S19 with S20
20	217	S11 near5 S15
21	104	S7 same S15
22	8454	((stack\$4 overlap\$6) near displa\$3)
23	231	S19 same S20
24	21	S23 same S20
25	505386	((integrate\$3 adj2 circuit\$3) IC)
26	110	two adj3 side\$4 near3 emission\$4
27	0	S20 and S41
28	824	dual near3 emission\$4

	Hits	Search Text
29	5	S20 and S39
30	4	S20 and S36
31	0	S20 near5 S36
32	509	dual adj2 emission\$4
33	343	S23 and S27
34	2	S23 and S20 and S27
35	3710	(metal\$3 near2 oxid\$3) with (insulat\$5 adj2 film\$4)
36	57	S20 near5 S31
37	161	S23 and S20 and S31
38	3	S23 same S20 and S31
39	531777	photograph\$4
40	183	S20 same S31

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	23290	(metal\$3 near2 film\$4) with (W Ti Ta Mo Nd Ni Co Zr Zn Ru Rh Pd Os Ir)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 06:53
L2	2700	(metal\$3 near2 film\$4) adj (W Ti Ta Mo Nd Ni Co Zr Zn Ru Rh Pd Os Ir)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 06:55
L3	922	(metal\$3 near2 film\$4) adj (Mo Nd Ni Co)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 06:54
L4	233	(metal\$3 near2 film\$4) adj (Mo)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 06:54
L5	163	(metal\$3 adj film\$4) adj (Mo)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 06:54
L6	1723	(metal\$3 adj film\$4) adj (W Ti Ta Mo Nd Ni Co Zr Zn Ru Rh Pd Os Ir)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 07:25
L7	1317	((integrate\$3 near3 circuit\$3) IC\$3) near2 (thin\$4 near2 film\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 06:56
L8	0	6 with 7	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 06:56

EAST Search History

L9	0	6 same 7	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 06:56
L10	3	6 and 7	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 07:26
L11	1	"5300735".pn. and ICs	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 07:23
L12	0	"5300735".pn. and (metal\$4 near2 oxid\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 07:24
L13	1	"5300735".pn. and (WO\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 07:24
L14	185	(metal\$3 adj oxid\$4) adj (WO\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 07:27
L15	0	14 and 7	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/11 07:26